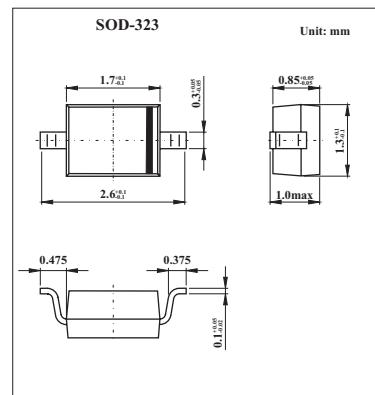


Schottky barrier Diodes

1PS76SB21

■ Features

- Ultra fast switching speed
- Low forward voltage
- Guard ring protected
- Very small plastic SMD package.



■ Absolute Maximum Ratings Ta = 25°C

PARAMATER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	VR			4	V
continuous forward current	VF			200	mA
non-repetitive peak forward current	I _{FSM}	t _p < 10 ms		1	A
storage temperature	T _{stg}		-65	+150	°C
junction temperature	T _j			125	°C

■ Electrical Characteristics Ta = 25°C

PARAMATER	SYMBOL	CONDITIONS	MIN.	MAX.	UNIT
forward volatge	V _F	I _F = 10 mA		300	mV
		I _F = 100 mA		420	mV
		I _F = 200 mA		550	mV
reverse current	I _R	V _R = 30 V; note 1		15	µ A
		V _R = 30 V; T _j = 100 °C, note 1		3	mA
diode capacitance	C _d	f = 1 MHz; V _R = 0 V;	40	50	pF
thermal resistance from junction to ambient	R _{thj-a}			450	K/W

Note

■ Marking

Marking	S1
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